

UNIVERSIT DEGLI STU DI TORINO

Scuola di Scienze della Natura Corso di Laurea Triennale in Fisica



# Characterization of the SiPMs for the scintillation detectors of IceCube

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#### IceCube – Gen 2

- The first gigaton detector ever built
- Search for neutrinos and cosmic rays from the most violent astrophysical sources
- Detection of particles using Antarctic's transparent ice and Cherenkov effect



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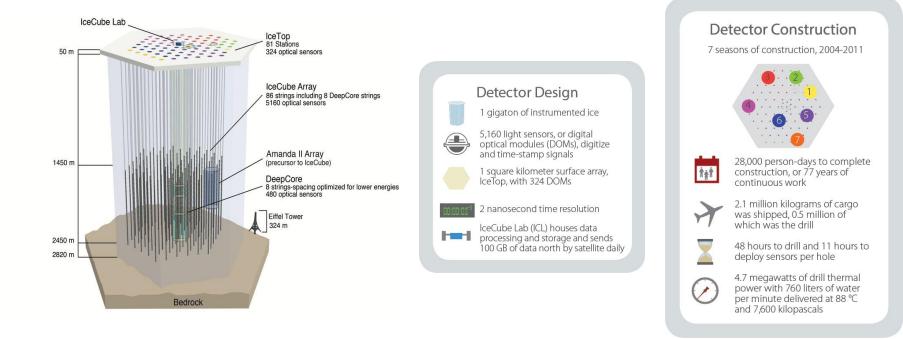
#### Ice Top

- A surface array of scintillation detectors used as a partial veto for the down-going background of penetrating muons
  - Detection of air showers with an energy resolution from Pev to Eev
  - 162 tanks of ice each instrumented with two standard lceCube sensors: two Digital Optical Modules (DOMs), a 10 inch photomultiplier tube (PMT) and electronics

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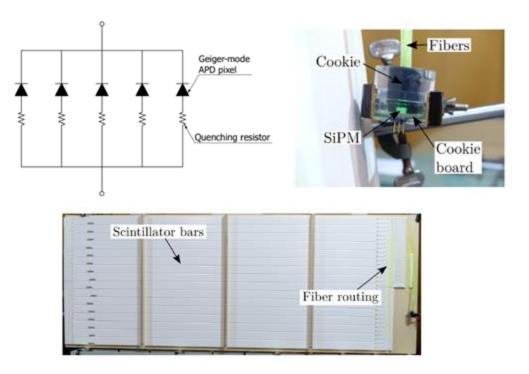




# SiPMs for the upgrade of IceTop

• SiPMs are **semiconductor photosensors** consisting of an array of avalanche photodiode (APD) microcells.

- The photons produced when crossing the **scintillator bars** are collected and guided via **wavelength-shifting fibers** to a SiPM.
- It is connected to a data acquisition board (microDAQ).
- Main characteristics: gain, IV curve, dark-count rate, crosstalk probability, PDE, temperature readout

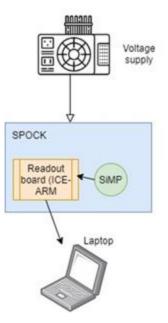




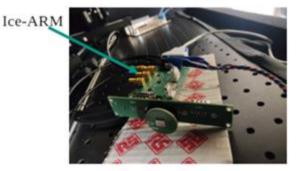


#### Internship project

- The analysis of the IV curve allows to obtain important parameters
- In the **operational zone** of the SiPM, it is possible to find a linearity between the output signal and the number of incident photons
- The setup: SPOCK (Single Photon Calibration Stand at Kit), +5V voltage supply, a Python script to control the output voltage
- For each SiPM, three sets of current and voltage values are collected. The output voltage ranges from 55 V to 75V.











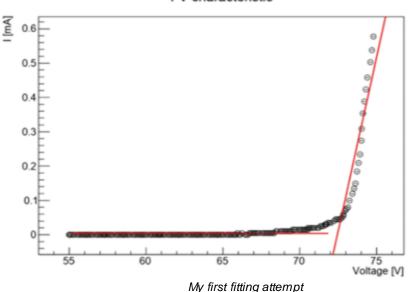
#### Analysis of IV characteristics

- Breakdown voltage: bias voltage of the SiPM when the SiPM's current increases rapidly.
- The overvoltage can be expressed as a function of the breakdown voltage:

 $V_{ov} = V_{bias} - V_{break;;}$ 

- A ROOTCern script finds the rapid increase of the current and fits the data points with two linear curves.
- The **intersection** between the curves corresponds to the breakdown voltage.

• The error of the breakdown voltage is obtained by propagation of the errors on the parameters of the lines.



#### I-V characteristic

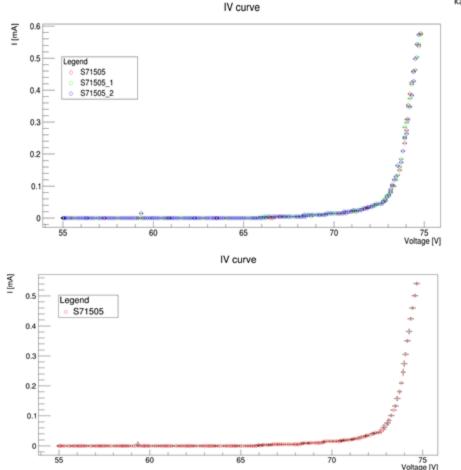


## **Multiple measurements**

- An average is calculated between corresponding values of current and voltage
- The error attributed on the average is the **standard deviation**

$$\sigma = \frac{1}{\sqrt{N}} \sqrt{\frac{\sum\limits_{i=1}^{N} (x_i - \overline{x})^2}{N-1}}$$

- A further **systematic error** of 0.1 V is added for the voltage value
- Each SiPM is given a serial number S7XXXX

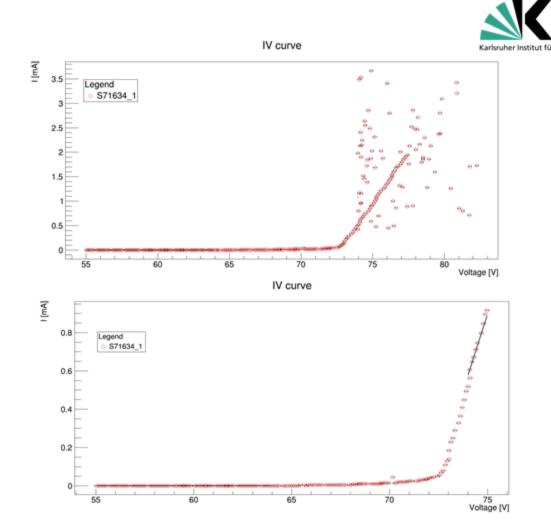






#### Analysis of scattered points

- When the applied voltage is higher than 75V, **instability effects** occur.
- The increased depletion zone of the APDs causes collisions between electron hole pairs and the semiconductor lattice of the SiPM.
- Data points above 75 V or those with a change of current higher than 0.5 mA between the previous point and the next one are removed.





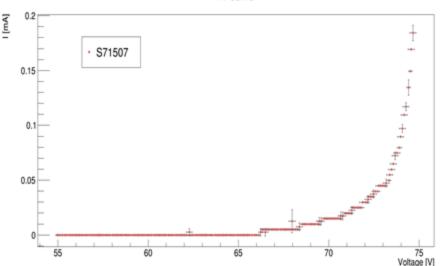


## Fitting the data

- There are two ways to consider specific data points for the regression.
- First method: the script analyzes the absolute change of current and voltage between points of a **set**:

Abschange =  $\frac{I(i+separation) - I(i)}{V(i+separation) - V(i)}$ 

- The separation represents the number of points constituting a data set
- The regression data on the left is taken up until the absolute change is higher than 0.02 mA/V
- The regression data on the right is taken up until the absolute change is lower than 0.06 mA/V.



#### IV curve



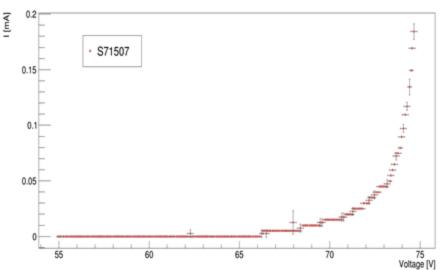
# Karlsruher Institut für Technologi

## Fitting the data

• Second method: the script analyzes the relative change of current and voltage between one set of points and the previous one.

$$Relchange = \frac{Abschange(i+1)}{Abschange(i)}$$

• The regression data on the right and on the left is taken up until this change differs from the previous one by 20%.

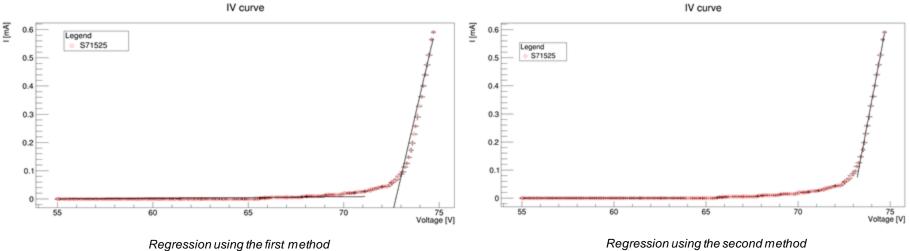


IV curve





## Fitting the data

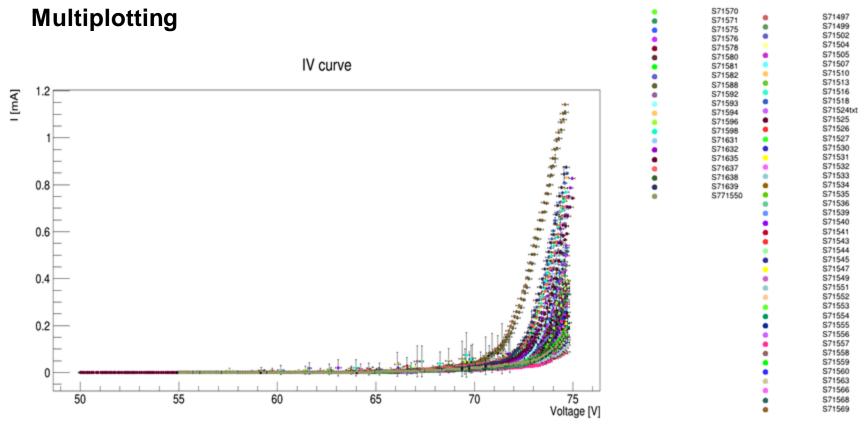


Regression using the second method

	Breakdown voltage (V)	Error (V)
1° Method	72	2
2° Method	72	1



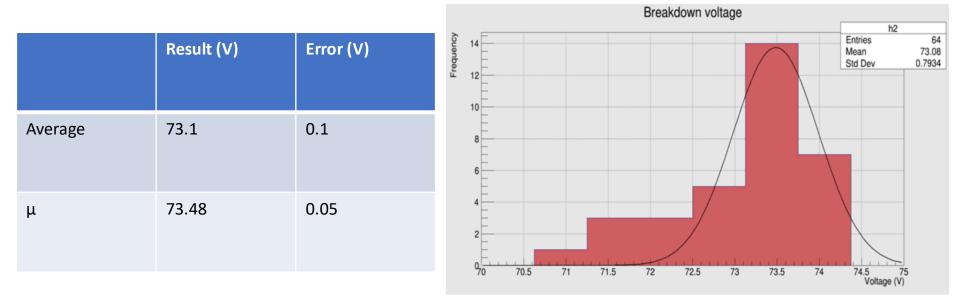








#### Analysis of breakdown voltage



 To work in the operational zone, for most of the SiPMs a bias voltage higher than µ should be applied



## Conclusion

The final version of the script:

• Plots the voltage and current measurements without entering them manually;

Automatically multiplots different SiRMs on the same canvas;

- Takes into consideration the scattered points on the canvas and deletes them;
- Analyzes the trend of the data points and fits them with two linear curves;
- Calculates the breakdown voltage and its error
- Collects the values of breakdown voltage and error in a .txt file



#### Outlooks

Other SiPM features are studied (cross-talk rate, PDE, dark counts);

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The distribution of breakdown voltage is useful to apply a proper bias voltage;

The Geiger zone lies between 73 V and 75 V;

Semiconductor effects should be studied to have a deeper knowledge of SiPMs' behaviour

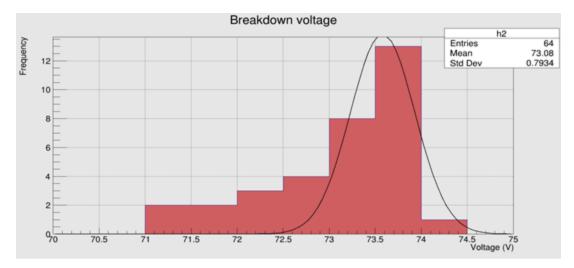


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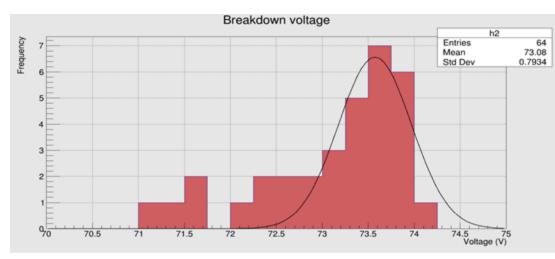
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x <sub>0</sub>	13 ± 1
x <sub>1</sub>	$73.58 \pm 0.03$
x <sub>2</sub>	0.35 ± 0.06



X <sub>0</sub>	6 ± 1
x <sub>1</sub>	$73.57 \pm 0.06$
X <sub>2</sub>	$0.40 \pm 0.09$





#### IV curve

